

IN THE SPECIFICATION:

Please replace the paragraph on page 3, lines 15-21, with the following paragraph:

In accordance with the principles of the present invention, a method of forming a by-pass capacitor on a multi-level metallization device is utilized to improve the capacitance per unit area of the by-pass capacitor. The method includes forming a first electrode in a first ~~metal-dielectric~~ layer of the multi-level metallization device and depositing a substantially thin ~~dielectric-insulator~~ material layer over the first ~~metal-dielectric~~ layer of the multi-level metallization device. The method also includes forming a second electrode ~~on~~-in a second ~~metal-dielectric~~ layer, where the second ~~metal-dielectric~~ layer is formed over the substantially thin ~~dielectric-insulator~~ material layer.

Please replace the paragraph on page 5, lines 15-20, with the following paragraph:

In another aspect, the present invention relates to a high-k constant MIM capacitor. The high-k constant MIM capacitor may comprise a lower electrode ~~in a first metal layer~~ of a VLSI device, a substantially thin layer of high-k insulator (e.g., silicon nitride, lead zirconate titanate ("PZT"), etc.) at an interface of the ~~first metal layer~~-lower electrode and a via, and an upper electrode ~~form in a second metal layer~~. The via provides a channel between the ~~second metal layer to~~-upper electrode and the high-k insulator.